NSN 5961-01-210-8895

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View Online at https://aerobasegroup.com/nsn/5961-01-210-8895

Inclosure Material:

Metal

Overall Length:

1.573 inches

Overall Height:

0.328 inches

Overall Width:

1.050 inches

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-3

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case and quality assurance level txv

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

180.0 collector to base voltage/static/emitter open and 150.0 collector to emitter voltage/static/base open and 6.0 emitter to base voltage,

static, collector open

Current Rating Per Characteristic:

Between 10.00 amperes source cutoff current and 25.00 amperes source cutoff current

Power Rating Per Characteristic:

200.0 watts small-signal input power, common-collector preset

Transfer Ratio:

120.0 static forward current transfer ratio, common-emitter

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius ambient air

Special Features:

Junction pattern arrangement: npn

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

2 pin and 1 case

Specification Data:

81349-mil-s-19500/509 government specification

Shelf Life:

NI/o

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Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

A110a0

